

ABSTRACT

A method for transferring an electrically active thin film from an initial substrate to a target substrate including: ion implantation through one face of the initial substrate to create a buried, embrittled film at a determined depth relative to the implanted face of the initial substrate, thus delimiting a thin film between the implanted face and the buried face; fastening the implanted face of the initial substrate with a face of the target substrate; separating the thin film from the remainder of the initial substrate at the level of the buried film; and thinning down the thin film transferred on the target substrate. The implantation dosage, energy, and current are chosen, during the ion implantation, so that concentration in implantation defects is less than a determined threshold, resulting in, within the thinned down thin film, a number of acceptor defects compatible with desired electrical properties of the thin film.